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Haronian

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[54] **MICRO-ELECTRO-MECHANICS SYSTEMS (MEMS)**

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[52] **U.S. Cl.** **73/774**; 73/777

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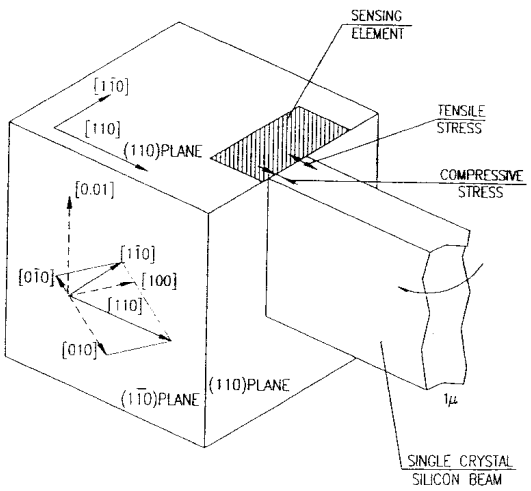
[57] **ABSTRACT**

A microelectronics deformation sensor including at least one stress sensor directly integrated on at least one of an extremity of a supported deformable structure and a support of the deformable structure, the deformable structure being constructed of a single crystal material, the at least one stress sensor sensing a stress in a vicinity of the extremity and thereby sensing a deformation of the deformable structure.

27 Claims, 24 Drawing Sheets